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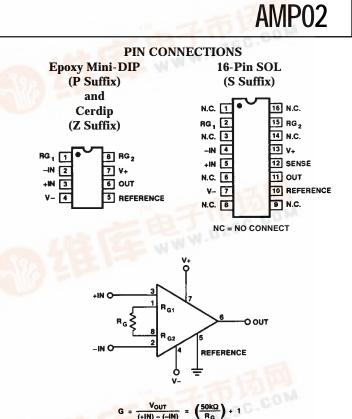
ANALOG DEVICES

High Accuracy 8-Pin Instrumentation Amplifier

FEATURES

Low Offset Voltage: 100 µV max Low Drift: 2 µV/°C max Wide Gain Range 1 to 10,000 High Common-Mode Rejection: 115 dB min High Bandwidth (G = 1000): 200 kHz typ Gain Equation Accuracy: 0.5% max Single Resistor Gain Set Input Overvoltage Protection Low Cost Available In Die Form

APPLICATIONS Differential Amplifier Strain Gauge Amplifier Thermocouple Amplifier RTD Amplifier Programmable Gain Instrumentation Amplifier Medical Instrumentation Data Acquisition Systems



GENERAL DESCRIPTION

The AMP02 is the first precision instrumentation amplifier available in an 8-pin package. Gain of the AMP02 is set by a single external resistor, and can range from 1 to 10,000. No gain set resistor is required for unity gain. The AMP02 includes an input protection network that allows the inputs to be taken 60 V beyond either supply rail without damaging the device.

Laser trimming reduces the input offset voltage to under 100 μ V. Output offset voltage is below 4 mV and gain accuracy is better than 0.5% for gain of 1000. PMI's proprietary thin-film resistor process keeps the gain temperature coefficient under 50 ppm/°C.

Due to the AMP02's design, its bandwidth remains very high over a wide range of gain. Slew rate is over 4 V/ μ s making the AMP02 ideal for fast data acquisition systems.

FOR SOL CONNECT SENSE TO OUTPUT

Figure 1. Basic Circuit Connections

A reference pin is provided to allow the output to be referenced to an external dc level. This pin may be used for offset correction or level shifting as required. In the 8-pin package, sense is internally connected to the output.

For an instrumentation amplifier with the highest precision, consult the AMP01 data sheet. For the highest input impedance and speed, consult the AMP05 data sheet.

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$\label{eq:specifications} \begin{array}{l} \textbf{AMPO2-SPECIFICATIONS} \\ \textbf{ELECTRICAL CHARACTERISTICS} (@V_{S} = \pm 15 \text{ V}, \text{ V}_{CM} = 0 \text{ V}, \text{ T}_{A} = +25^{\circ}\text{C}, \text{ unless otherwise noted.} \end{array}$

		$V_{\rm CM} = 10^{-1} V_{\rm CM} = 0^{-1}$		AMP02E		A	AMP02F		
Parameter OFFSET VOLTAGE	Symbol	Conditions	Min	Тур	Max	Min	Тур	Max	Units
OFFSET VOLTAGE Input Offset Voltage Drift Output Offset Voltage Output Offset Voltage Drift Power Supply Rejection	V _{IOS} TCV _{IOS} V _{OOS} TCV _{OOS} PSR	$\begin{array}{l} T_{A}=+25^{\circ}C\\ -40^{\circ}C\leq T_{A}\leq+85^{\circ}C\\ -40^{\circ}C\leq T_{A}\leq+85^{\circ}C\\ T_{A}=+25^{\circ}C\\ -40^{\circ}C\leq T_{A}\leq+85^{\circ}C\\ -40^{\circ}C\leq T_{A}\leq+85^{\circ}C\\ V_{S}=\pm4.8\ V\ to\ \pm18\ V\\ G\ =\ 100,\ 1000\\ G\ =\ 10\\ G\ =\ 1\end{array}$	115 100 80	20 50 0.5 1 4 50 125 110 90	100 200 2 4 10 100	110 95 75	40 100 1 2 9 100 115 100 80	200 350 4 8 20 200	μV μV/°C mV mV μV/°C dB dB dB
		$ \begin{array}{l} V_{\rm S} = \pm 4.8 \ V \ to \pm 18 \ V \\ -40^{\circ}{\rm C} \leq T_{\rm A} \leq +85^{\circ}{\rm C} \\ {\rm G} = 1000, \ 100 \\ {\rm G} = 10 \\ {\rm G} = 1 \end{array} $	110 95 75	120 110 90		105 90 70	110 95 75		dB dB dB dB
INPUT CURRENT Input Bias Current Input Bias Current Drift Input Offset Current Input Offset Current Drift	$\begin{matrix}I_{B}\\TCI_{B}\\I_{OS}\\TCI_{OS}\end{matrix}$	$\begin{array}{l} T_{A}=+25^{\circ}C\\ -40^{\circ}C\leq T_{A}\leq+85^{\circ}C\\ T_{A}=+25^{\circ}C\\ -40^{\circ}C\leq T_{A}\leq+85^{\circ}C \end{array}$		2 150 1.2 9	10 5		4 250 2 15	20 10	nA pA/°C nA pA/°C
INPUT Input Resistance Input Voltage Range Common-Mode Rejection	R _{IN} IVR CMR	Differential, $G \le 1000$ Common-Mode, $G = 1000$ $T_A = +25^{\circ}C$ (Note 1) $V_{CM} = \pm 11 V$	±11	10 16.5		±11	10 16.5		$\begin{array}{c} G\Omega\\ G\Omega\\ V\end{array}$
		$\begin{array}{l} G = 1000, \ 100 \\ G = 10 \\ G = 1 \\ V_{CM} = \pm 11 \ V \end{array}$	115 100 80	120 115 95		110 95 75	115 110 90		dB dB dB
		$\begin{array}{l} -40^{\circ}C \leq T_{A} \leq +85^{\circ}C \\ G = 100, \ 1000 \\ G = 10 \\ G = 1 \end{array}$	110 95 75	120 110 90		105 90 70	115 105 85		dB dB dB
GAIN Gain Equation Accuracy Gain Range	$G = \frac{50 \text{ k}\Omega}{R_G} + 1$ G	G = 1000 G = 100 G = 10 G = 1	1		0.50 0.30 0.25 0.02 10k	1		0.70 0.50 0.40 0.05 10k	% % % V/V
Nonlinearity Temperature Coefficient	G _{TC}	$\begin{array}{l} G = 1 \ \text{to} \ 1000 \\ 1 \leq G \leq 1000 \ (\text{Notes } 2, \ 3) \end{array}$		0.006 20	50		0.006 20	50	% ppm/°C
OUTPUT RATING Output Voltage Swing Positive Current Limit Negative Current Limit	V _{OUT}	$\begin{array}{l} T_A=+25^\circ C,\ R_L=1\ k\Omega\\ R_L=1\ k\Omega,\ -40^\circ C\leq T_A\leq+85^\circ C\\ Output-to-Ground\ Short\\ Output-to-Ground\ Short \end{array}$	±12 ±11	$^{\pm 13}_{\pm 12}_{22}_{32}$		±12 ±11	$^{\pm 13}_{\pm 12}_{22}_{32}$		V V mA mA
NOISE Voltage Density, RTI Noise Current Density, RTI Input Noise Voltage	e _n i _n e _n p-p	$ f_{O} = 1 \ \text{kHz} \\ G = 1000 \\ G = 100 \\ G = 10 \\ G = 1 \\ f_{O} = 1 \ \text{kHz}, \ G = 1000 \\ 0.1 \ \text{Hz} \ \text{to} \ 10 \ \text{Hz} $		9 10 18 120 0.4			9 10 18 120 0.4		$\begin{array}{l} nV/\sqrt{Hz}\\ nV/\sqrt{Hz}\\ nV/\sqrt{Hz}\\ nV/\sqrt{Hz}\\ nV/\sqrt{Hz}\\ pA/\sqrt{Hz} \end{array}$
		G = 1000 G = 100 G = 10		0.4 0.5 1.2			0.4 0.5 1.2		μV p-p μV p-p μV p-p
DYNAMIC RESPONSE Small-Signal Bandwidth (-3 dB) G = 100, 1000 Slew Rate	BW SR	G = 1 G = 10 $G = 10, R_1 = 1 k\Omega$	4	1200 300 200 6		4	1200 300 200 6		kHz kHz kHz V/µs
Settling Time	ts	To $0.01\% \pm 10$ V Step G = 1 to 1000		10		<u> </u>	10		μs
SENSE INPUT Input Resistance Voltage Range	R _{IN}			25 ±11			25 ±11		kΩ V
REFERENCE INPUT Input Resistance Voltage Range Gain to Output	R _{IN}			50 ±11 1			50 ±11 1		kΩ V V/V

			AMP02E		AMP02F				
Parameter	Symbol	Conditions	Min	Тур	Max	Min	Тур	Max	Units
POWER SUPPLY Supply Voltage Range Supply Current	V _S I _{SY}	$\begin{array}{l} T_{A}=+25^{\circ}C\\ -40^{\circ}C\leq T_{A}\leq+85^{\circ}C \end{array}$	±4.5	5 5	$ \pm 18 \\ 6 \\ 6 \\ 6 \\ $	± 4.5	5 5	$\begin{array}{c}\pm 18\\6\\6\end{array}$	V mA mA

NOTES

¹Input voltage range guaranteed by common-mode rejection test. ²Guaranteed by design.

³Gain tempco does not include the effects of external component drift.

Specifications subject to change without notice.

ABSOLUTE MAXIMUM RATINGS

Supply Voltage±18 V
Common-Mode Input Voltage . $[(V-) - 60 V]$ to $[(V+) + 60 V]$
Differential Input Voltage \dots [(V–) – 60 V] to [(V+) + 60 V]
Output Short-Circuit DurationContinuous
Operating Temperature Range40°C to +85°C
Storage Temperature Range
Function Temperature Range65°C to +150°C
Lead Temperature (Soldering, 10 sec) +300°C

Package Type	$\theta_{JA}{}^2$	θ _{JC}	Units	
8-Pin Plastic DIP (P)	96	37	°C/W	
16-Pin SOL (S)	92	27	°C/W	

NOTES

¹Absolute maximum ratings apply to both DICE and packaged parts, unless otherwise noted.

 $^2\theta_{JA}$ is specified for worst case mounting conditions, i.e., θ_{JA} is specified for device in socket for P-DIP package; θ_{JA} is specified for device soldered to printed circuit board for SOL package.

ORDERING	GUIDE
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Model	V _{IOS} max @ T _A = +25°C	000	Temperature Range	Package Description
AMP02EP AMP02FP AMP02AZ/883C AMP02FS AMP02GBC AMP02FS-REEL	100 μV 200 μV 200 μV 200 μV 200 μV	4 mV 8 mV 10 mV 8 mV 8 mV	-40°C to +85°C -40°C to +85°C -55°C to +125°C -40°C to +85°C -40°C to +85°C	8-Pin Plastic DIP 8-Pin Plastic DIP 8-Pin Cerdip 16-Pin SOIC Die 16-Pin SOIC

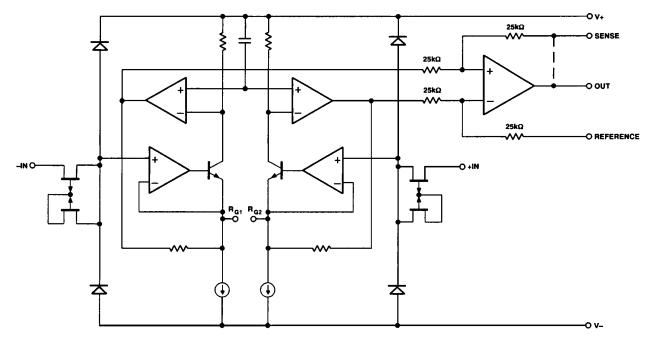
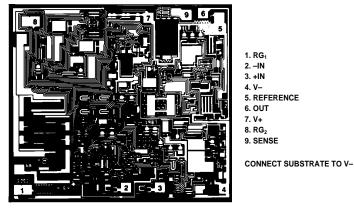


Figure 2. Simplified Schematic



DIE SIZE 0.103 X 0.116 inch, 11,948 sq. mils (2.62 X 2.95 mm, 7.73 sq. mm)

Dice Characteristics

WAFER TEST LIMITS at V_s = ± 15 V, V_{CM} = 0 V, T_A = +25°C, unless otherwise noted.

Parameter	Symbol	Conditions	AMP02 GBC Limits	Units
Input Offset Voltage	V _{IOS}		200	μV max
Output Offset Voltage	V _{oos}		8	mV max
Power Supply Rejection	PSR	$V_{S} = \pm 4.8 V \text{ to } \pm 18 V$ G = 1000 G = 100 G = 10 G = 1	110 110 95 75	dB min
Input Bias Current	I _B		20	nA max
Input Offset Current	I _{OS}		10	nA max
Input Voltage Range	IVR	Guaranteed by CMR Tests	±11	V min
Common-Mode Rejection	CMR	$V_{CM} = \pm 11 V$ G = 1000 G = 100 G = 10 G = 1	110 110 95 75	dB min
Gain Equation Accuracy		$G = \frac{50 \ k\Omega}{R_G} + 1, \ G = 1000$	0.7	% max
Output Voltage Swing	V _{OUT}	$R_L = 1 k\Omega$	±12	V min
Supply Current	I _{SY}		6	mA max

NOTE

Electrical tests are performed at wafer probe to the limits shown. Due to variations in assembly methods and normal yield loss, yield after packaging is not guaranteed for standard product dice. Consult factory to negotiate specifications based on dice lot qualifications through sample lot assembly and testing.

CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the AMP02 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



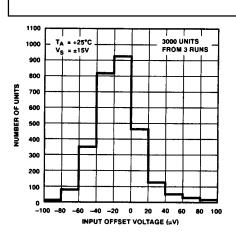


Figure 3. Typical Distribution of Input Offset Voltage

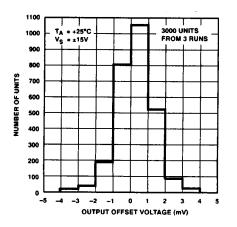


Figure 6. Typical Distribution of Output Offset Voltage

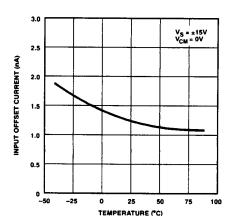


Figure 9. Input Offset Current vs. Temperature

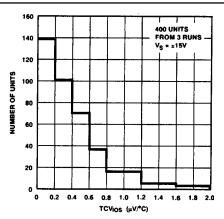


Figure 4. Typical Distribution of TCV_{IOS}

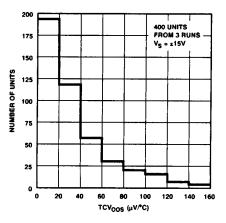


Figure 7. Typical Distribution of TCV_{00S}

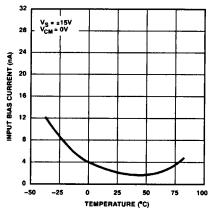


Figure 10. Input Bias Current vs. Temperature

Typical Performance Characteristics-AMP02

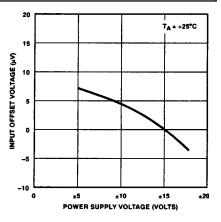


Figure 5. Input Offset Voltage Change vs. Supply Voltage

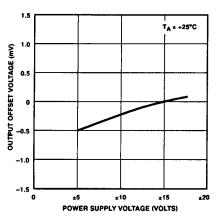


Figure 8. Output Offset Voltage Change vs. Supply Voltage

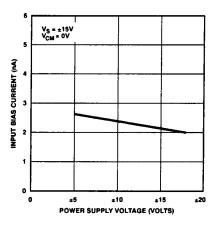


Figure 11. Input Bias Current vs. Supply Voltage

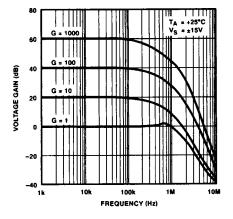


Figure 12. Closed-Loop Voltage Gain vs. Frequency

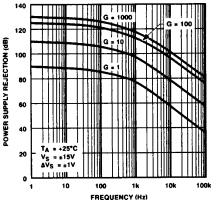


Figure 15. Positive PSR vs. Frequency

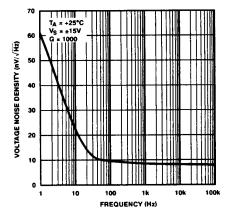


Figure 18. Voltage Noise Density vs. Frequency

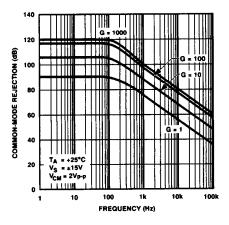


Figure 13. Common-Mode Rejection vs. Frequency

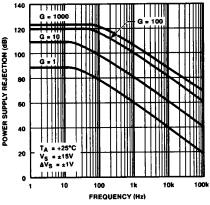


Figure 16. Negative PSR vs. Frequency

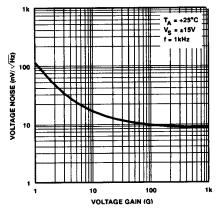


Figure 19. RTI Voltage Noise Density vs. Gain

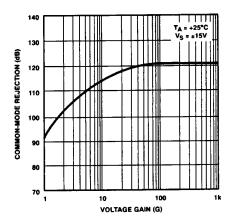


Figure 14. Common-Mode Rejection vs. Voltage Gain

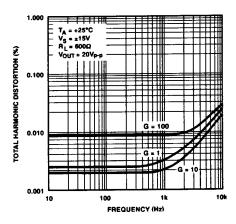


Figure 17. Total Harmonic Distortion vs. Frequency

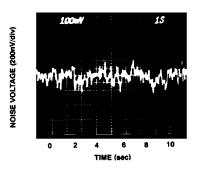


Figure 20. 0.1 Hz to 10 Hz Noise $A_V = 1000$

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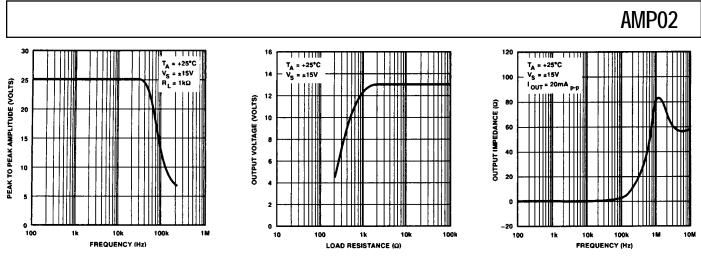


Figure 21. Maximum Output Swing vs. Frequency

Figure 22. Maximum Output Voltage vs. Load Resistance

Figure 23. Closed Loop Output Impedance vs. Frequency

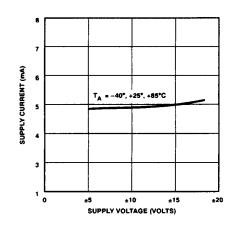


Figure 24. Supply Current vs. Supply Voltage

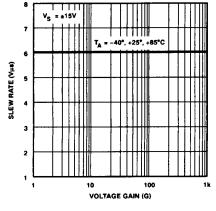


Figure 25. Slew Rate vs. Voltage Gain

APPLICATIONS INFORMATION INPUT AND OUTPUT OFFSET VOLTAGES

Instrumentation amplifiers have independent offset voltages associated with the input and output stages. The input offset component is directly multiplied by the amplifier gain, whereas output offset is independent of gain. Therefore, at low gain, output-offset-errors dominate, while at high gain, input-offset-errors dominate. Overall offset voltage, V_{OS} , referred to the output (RTO) is calculated as follows:

$$V_{OS}$$
 (RTO) = ($V_{IOS} \times G$) + V_{OOS}

where V_{IOS} and V_{OOS} are the input and output offset voltage specifications and G is the amplifier gain.

The overall offset voltage drift TCV_{OS} , referred to the output, is a combination of input and output drift specifications. Input offset voltage drift is multiplied by the amplifier gain, G, and summed with the output offset drift:

$$TCV_{OS}$$
 (RTO) = ($TCV_{IOS} \times G$) + TCV_{OOS}

where TCV_{IOS} is the input offset voltage drift, and TCV_{OOS} is the output offset voltage drift. Frequently, the amplifier drift is referred back to the input (RTI) which is then equivalent to an input signal change:

$$TCV_{OS} (RTI) = TCV_{IOS} + \frac{TCV_{OOS}}{G}$$

For example, the maximum input-referred drift of an AMP02EP set to G = 1000 becomes:

$$TCV_{OS} (RTI) = 2\,\mu V/^{\circ}C + \frac{100\,\mu V/^{\circ}C}{1000} = 2.1\,\mu V/^{\circ}C$$

INPUT BIAS AND OFFSET CURRENTS

Input transistor bias currents are additional error sources which can degrade the input signal. Bias currents flowing through the signal source resistance appear as an additional offset voltage. Equal source resistance on both inputs of an IA will minimize offset changes due to bias current variations with signal voltage and temperature. However, the difference between the two bias currents, the input offset current, produces an error. The magnitude of the error is the offset current times the source resistance.

A current path must always be provided between the differential inputs and analog ground to ensure correct amplifier operation. Floating inputs, such as thermocouples, should be grounded close to the signal source for best common-mode rejection.

GAIN

The AMP02 only requires a single external resistor to set the voltage gain. The voltage gain, G, is:

 $G = \frac{50 \, k\Omega}{R_G} + 1$

and

$$R_G = \frac{50 \, k\Omega}{G - 1}$$

The voltage gain can range from 1 to 10,000. A gain set resistor is not required for unity-gain applications. Metal-film or wirewound resistors are recommended for best results.

The total gain accuracy of the AMP02 is determined by the tolerance of the external gain set resistor, R_G , combined with the gain equation accuracy of the AMP02. Total gain drift combines the mismatch of the external gain set resistor drift with that of the internal resistors (20 ppm/°C typ). Maximum gain drift of the AMP02 independent of the external gain set resistor is 50 ppm/°C.

All instrumentation amplifiers require attention to layout so thermocouple effects are minimized. Thermocouples formed between copper and dissimilar metals can easily destroy the TCV_{OS} performance of the AMP02 which is typically $0.5 \ \mu V/^{\circ}C$. Resistors themselves can generate thermoelectric EMFs when mounted parallel to a thermal gradient.

The AMP02 uses the triple op amp instrumentation amplifier configuration with the input stage consisting of two transimpedance amplifiers followed by a unity-gain differential amplifier. The input stage and output buffer are laser-trimmed to increase gain accuracy. The AMP02 maintains wide bandwidth at all gains as shown in Figure 26. For voltage gains greater than 10, the bandwidth is over 200 kHz. At unity-gain, the bandwidth of the AMP02 exceeds 1 MHz.

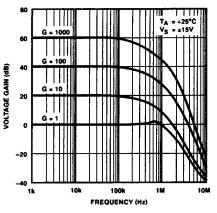


Figure 26. The AMP02 Keeps Its Bandwidth at High Gains

COMMON-MODE REJECTION

Ideally, an instrumentation amplifier responds only to the difference between the two input signals and rejects common-mode voltages and noise. In practice, there is a small change in output voltage when both inputs experience the same common-mode voltage change; the ratio of these voltages is called the commonmode gain. Common-mode rejection (CMR) is the logarithm of the ratio of differential-mode gain to common-mode gain, expressed in dB. Laser trimming is used to achieve the high CMR of the AMP02.

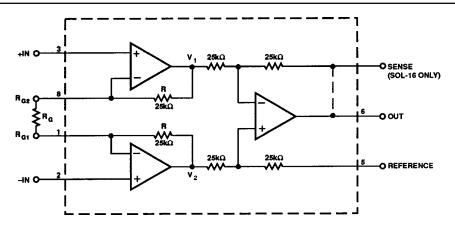


Figure 27. Triple Op Amp Topology of the AMP02

Figure 27 shows the triple op amp configuration of the AMP02. With all instrumentation amplifiers of this type, it is critical not to exceed the dynamic range of the input amplifiers. The amplified differential input signal and the input common-mode voltage must not force the amplifier's output voltage beyond ± 12 V (V_S = ± 15 V) or nonlinear operation will result.

The input stage amplifier's output voltages at V, and V₂ equals:

$$V_{I} = -\left(1 + \frac{2R}{R_{G}}\right)\frac{V_{D}}{2} + V_{CM}$$
$$= -G\frac{V_{D}}{2} + V_{CM}$$
$$V_{2} = \left(1 + \frac{2R}{R_{G}}\right)\frac{V_{D}}{2} + V_{CM}$$
$$= G\frac{V_{D}}{2} + V_{CM}$$

where

 V_D = Differential input voltage

$$= (+IN) - (-IN)$$

 V_{CM} = Common-mode input voltage

G = Gain of instrumentation amplifier

If V_1 and V_2 can equal ± 12 V maximum, then the common-mode input voltage range is:

$$CMVR = \pm \left(12 V - \frac{GV_D}{2}\right)$$

GROUNDING

The majority of instruments and data acquisition systems the separate grounds for analog and digital signals. Analog ground may also be divided into two or more grounds which will be tied together at one point, usually the analog power-supply ground. In addition, the digital and analog grounds may be joined, normally at the analog ground pin on the A to D converter. Follow this basic practice is essential for good circuit performance.

Mixing grounds causes interactions between digital circuits and the analog signals. Since the ground returns have finite resistance and inductance, hundreds of millivolts can be develop between the system ground and the data acquisition components. Using separate ground returns minimizes the current flow in the sensitive analog return path to the system ground point. Consequently, noisy ground currents from logic gates do interact with the analog signals.

Inevitably, two or more circuits will be joined together with their grounds at differential potentials. In these situations, the differential input of an instrumentation amplifier, with its high CMR, can accurately transfer analog information from one circuit to another.

SENSE AND REFERENCE TERMINALS

The sense terminal completes the feedback path for the instrumentation amplifier output stage and is internally connected directly to the output. For SOL devices, connect the sense terminal to the output. The output signal is specified with respect to the reference terminal, which is normally connected to analog ground. The reference may also be used for offset correction level shifting. A reference source resistance will reduce the common-mode rejection by the ratio of 25 k Ω/R_{REF} . If the reference source resistance is 1 Ω , then the CMR will be reduced 88 dB (25 k $\Omega/1 \Omega = 88$ dB).

OVERVOLTAGE PROTECTION

Instrumentation amplifiers invariably sit at the front end of instrumentation systems where there is a high probability of exposure to overloads. Voltage transients, failure of a transducer, or removal of the amplifier power supply while the signal source is connected may destroy or degrade the performance of an unprotected device. A common technique used is to place limiting resistors in series with each input, but this adds noise. The AMP02 includes internal protection circuitry that limits the input current to ± 4 mA for a 60 V differential overload (see Figure 28) with power off, ± 2.5 mA with power on.

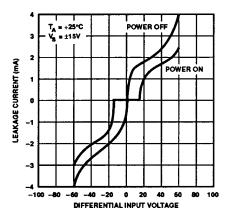


Figure 28. AMP02's Input Protection Circuitry Limits Input Current During Overvoltage Conditions

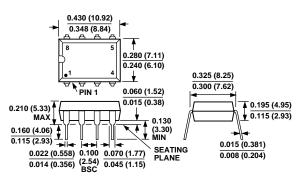
POWER SUPPLY CONSIDERATIONS

Achieving the rated performance of precision amplifiers in a practical circuit requires careful attention to external influences. For example, supply noise and changes in the nominal voltage directly affect the input offset voltage. A PSR of 80 dB means that a change of 100 mV on the supply, not an uncommon value, will produce a 10 μ V input offset change. Consequently, care should be taken in choosing a power unit that has a low output noise level, good line and load regulation, and good temperature stability. In addition, each power supply should be properly bypassed.

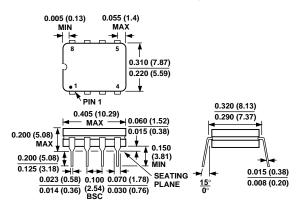
OUTLINE DIMENSIONS

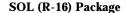
Dimensions shown in inches and (mm).

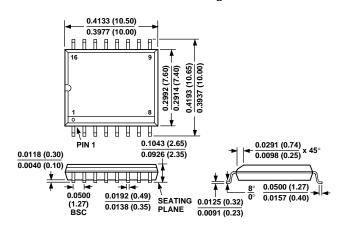
Mini-Dip (N-8) Package



Cerdip (Q-8) Package







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